

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Cancelled)
2. (Cancelled).
3. (Currently Amended) The semiconductor light emitting device according to claim ~~[[1]]~~ 13, wherein the cylindrical vacancies are formed such that the cylindrical vacancies of adjacent porous structures are oriented in different directions.
4. (Currently Amended) The semiconductor light emitting device according to claim ~~[[1]]~~ 13, wherein the mesa section includes a surface emission structure having an electrode in a top portion and comprises a semiconductor layer provided with an active layer having a quantum well structure constituted by a compound semiconductor, and
a pad to come in contact with the electrode is provided on the inorganic insulating film.
5. (Cancelled).

6. (Cancelled) .

7. (Cancelled) .

8. (Cancelled) .

9. (Cancelled).

10. (Currently Amended) The semiconductor light emitting device according to claim ~~[[1]]~~ 13, wherein the mesa section includes a surface emission structure having an electrode in a top portion and comprises a semiconductor layer provided with an active layer having a quantum well structure constituted by a compound semiconductor, and

a pad to come in contact with the electrode is provided on the inorganic insulating film.

11. (Previously Presented) The semiconductor light emitting device according to claim 3, wherein the mesa section includes a surface emission structure having an electrode in a top portion and comprises a semiconductor layer provided with an active layer having a quantum well structure constituted by a compound semiconductor, and

a pad to come in contact with the electrode is provided on the inorganic insulating film.

12. (Currently Amended) The semiconductor light emitting device according to claim [[1]] 13, wherein the inorganic insulating film is a sintered inorganic insulating film.

13. (Currently Amended) A semiconductor light emitting device comprising:
a mesa section having at least a sandwich structure of an n-type clad layer, an active layer and a p-type clad layer which are constituted by compound semiconductor layers formed on a substrate;

an insulating film of polyimide covering the mesa section excluding a contact region; and

an inorganic insulating film having a porous area defined by cylindrical vacancies so as to cover the ~~mesa section~~ insulating film excluding the contact region,

wherein the inorganic insulating film has a vacancy rate of 50% or more while being oriented substantially in parallel with a surface of the substrate, and wherein the vacancies are arranged at periodic intervals, and

wherein the cylindrical vacancies are formed such that the cylindrical vacancies of adjacent porous structures are oriented in different directions.

14. (New) A semiconductor light emitting device comprising:
a mesa section having at least a sandwich structure of an n-type clad layer, an active layer and a p-type clad layer which are constituted by compound semiconductor layers formed on a substrate;

an insulating film of polyimide covering the mesa section excluding a contact region; and

an inorganic insulating film having a porous area defined by cylindrical vacancies so as to cover the insulating film excluding the contact region,

wherein the inorganic insulating film has a vacancy rate of 50% or more while being oriented substantially in parallel with a surface of the substrate, and wherein the vacancies are arranged at periodic intervals, and

wherein the mesa section surrounded by a trench and the trench is filled with the inorganic insulating film.

15. (New) A semiconductor light emitting device comprising:

a mesa section having at least a sandwich structure of an n-type clad layer, an active layer and a p-type clad layer which are constituted by compound semiconductor layers formed on a substrate;

an insulating film of polyimide covering the mesa section excluding a contact region; and

an inorganic insulating film having a porous area defined by cylindrical vacancies so as to cover the insulating film excluding the contact region,

wherein the inorganic insulating film has a vacancy rate of 50% or more while being oriented substantially in parallel with a surface of the substrate, and wherein the vacancies are arranged at periodic intervals, and

wherein the electrode formed into a ring shape having an opening in a center portion of the electrode.